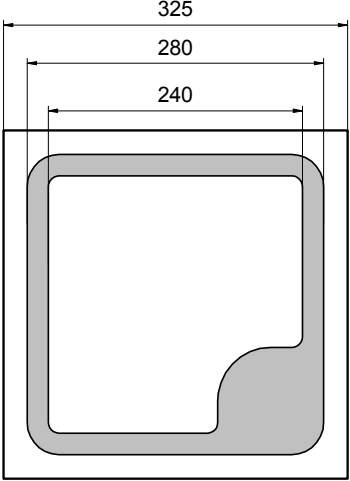


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up

 <p style="text-align: center;">LED-04</p>	typ. dimensions (μm)
	<p><u>typ. thickness</u> 150 (± 25) μm</p> <p><u>cathode</u> gold alloy, 1.5 μm</p> <p><u>anode</u> gold alloy, 0.5 μm, dotted, 25% covered</p>

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.7	2.0	V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5			V
Radiant power ¹	$I_F = 20 \text{ mA}$	Φ_e	2.2	3.0		mW
Radiant power ²	$I_F = 20 \text{ mA}$	Φ_e		6.0		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	760	770	780	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		30		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		40		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-770-25-1				

Packing: Chips on adhesive film with wire-bond side on top